

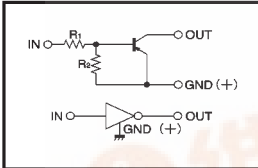
Digital transistors (built-in resistors)

DTA144WE / DTA144WUA / DTA144WKA / DTA144WSA

●Features

- 1) Built-in bias resistors enable the configuration of an inverter circuit without connecting external input resistors.
- 2) The bias resistors consist of thin-film resistors with complete isolation to allow positive biasing of the input, and parasitic effects are almost completely eliminated.
- 3) Only the on / off conditions need to be set for operation, making device design easy.
- 4) Higher mounting densities can be achieved.

●Circuit schematic



●Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit	
Supply voltage	V _{cc}	-50	V	
Input voltage	V _i	-40~+10	V	
Output current	I _o	-30	mA	
	I _{c(Max)}	-100		
Power dissipation	Pd	150	mW	
		DTA144WUA / DTA144WKA		200
		DTA144WSA		300
Junction temperature	T _j	150	°C	
Storage temperature	T _{stg}	-55~+150	°C	

●Package, marking, and packaging specifications

Part No.	DTA144WE	DTA144WUA	DTA144WKA	DTA144WSA
Package	EMT3	UMT3	SMT3	SPT
Marking	76	78	76	—
Packaging code	TL	T106	T146	TP
Basic ordering unit (pieces)	3000	3000	3000	5000

●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Input voltage	V _{i(off)}	—	—	-0.8	V	V _{cc} =-5V, I _o =-100 μA
	V _{i(on)}	-4	—	—		V _o =-0.3V, I _o =-2mA
Output voltage	V _{o(on)}	—	-0.1	-0.3	V	I _o =-10mA, I _i =-0.5mA
Input current	I _i	—	—	-0.16	mA	V _i =-5V
Output current	I _{o(off)}	—	—	-0.5	μA	V _{cc} =-50V, V _i =0V
DC current gain	G _i	56	—	—	—	I _o =-5mA, V _o =-5V
Input resistance	R _i	32.9	47	61.1	kΩ	—
Resistance ratio	R ₂ /R ₁	0.37	0.47	0.57	—	—
Transition frequency	f _r	—	250	—	MHz	V _{CE} =-10V, I _E =5mA, f=100MHz *

* Transition frequency of the device.

(94S-579-144W)

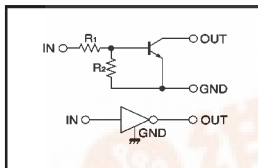
Digital transistors (built-in resistors)

DTC144WE / DTC144WUA / DTC144WKA / DTC144WSA

●Features

- 1) Built-in bias resistors enable the configuration of an inverter circuit without connecting external input resistors.
- 2) The bias resistors consist of thin-film resistors with complete isolation to allow negative biasing of the input, and parasitic effects are almost completely eliminated.
- 3) Only the on / off conditions need to be set for operation, making device design easy.
- 4) Higher mounting densities can be achieved.

●Circuit schematic



●Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit	
Supply voltage	V _{cc}	50	V	
Input voltage	V _i	-10~+40	V	
Output current	I _o	30	mA	
	I _{c(Max)}	100		
Power dissipation	Pd	150	mW	
		DTC144WUA / DTC144WKA		200
		DTC144WSA		300
Junction temperature	T _j	150	°C	
Storage temperature	T _{stg}	-55~+150	°C	

●Package, marking, and packaging specifications

Part No.	DTC144WE	DTC144WUA	DTC144WKA	DTC144WSA
Package	EMT3	UMT3	SMT3	SPT
Marking	86	86	86	—
Packaging code	TL	T106	T146	TP
Basic ordering unit (pieces)	3000	3000	3000	5000

●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Input voltage	V _{i(off)}	—	—	0.8	V	V _{cc} =5V, I _o =100 μA
	V _{i(on)}	4	—	—		V _o =0.3V, I _o =2mA
Output voltage	V _{o(on)}	—	0.1	0.3	V	I _o =10mA, I _i =0.5mA
Input current	I _i	—	—	0.16	mA	V _i =5V
Output current	I _{o(off)}	—	—	0.5	μA	V _{cc} =50V, V _i =0V
DC current gain	G _i	56	—	—	—	I _o =5mA, V _o =5V
Input resistance	R _i	32.9	47	61.1	kΩ	—
Resistance ratio	R ₂ /R ₁	0.37	0.47	0.57	—	—
Transition frequency	f _r	—	250	—	MHz	V _{CE} =10V, I _E =-5mA, f=100MHz *

* Transition frequency of the device.